

MITSUBISHI SEMICONDUCTOR <GaAs FET>  
**MGFS48B2122**

2.11 - 2.17 GHz BAND 60W GaAs FET

**DESCRIPTION**

The MGFS48B2122 is a 60W push-pull type GaAs Power FET especially designed for use in 2.11 - 2.17GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

**FEATURES**

- Push-pull configuration
- High output power  
Pout = 60W (TYP.) @ f=2.17 GHz
- High power gain  
GLP = 12 dB (TYP.) @ f=2.17GHz
- High power added efficiency  
P.A.E. = 48 % (TYP.) @ f=2.17GHz

**APPLICATION**

2.11-2.17GHz band power amplifier for W-CDMA Base Station

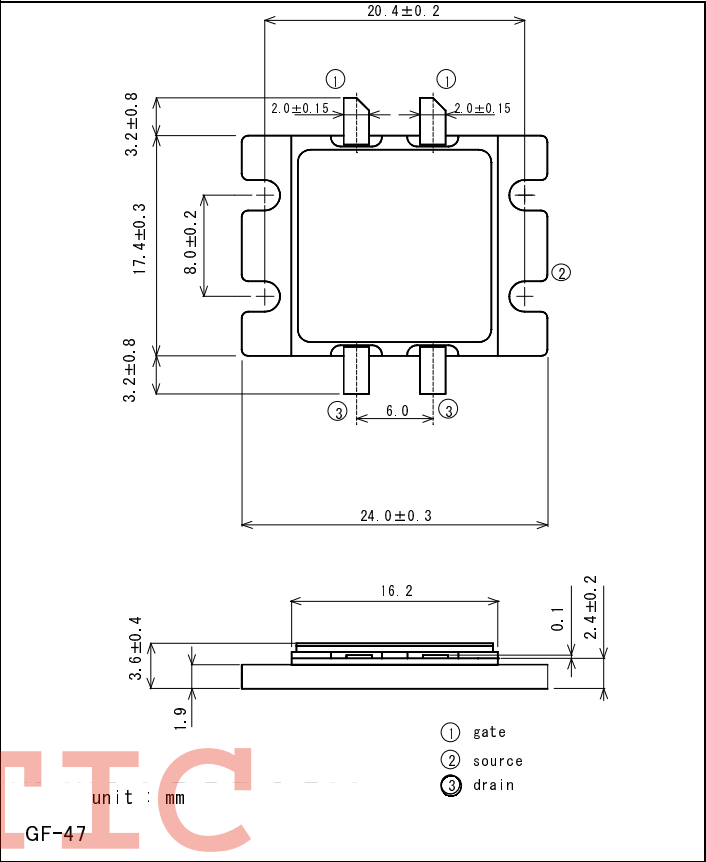
**QUALITY GRADE**

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**RECOMMENDED BIAS CONDITIONS**

VDS = 12 (V)  
ID = 2.0 (A)  
RG=20 (ohm) for each gate

OUTLINE



**ABSOLUTE MAXIMUM RATINGS** (Ta=25deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-20	V
VGSO	Gate to source voltage	-10	V
PT *1	Total power dissipation	125	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

\*1 : Tc=25deg.C

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**ELECTRICAL CHARACTERISTICS** (Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
GLP	Linear power gain	Pin=22dBm	11	12	-	dB
Pout	Output power	VDS=12V, ID(RF off)=2.0A	47	48	-	dBm
ID(RF)	Drain current	Pin=39dBm	-	11	15	A
P.A.E.	Power added efficiency	f=2.17GHz	-	48	-	%
Rth (ch-c)	Thermal resistance	Channel to Case	-	1	1.2	deg.C/W



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